

Vishay Semiconductors

Silicon NPN Phototransistor, RoHS Compliant



DESCRIPTION

VEMT3700 is a high speed silicon NPN epitaxial planar phototransistor in a miniature PLCC-2 package for surface mounting on printed boards. The device is sensitive to visible and near infrared radiation.

FEATURES

• Package type: surface mount

• Package form: PLCC-2



- High photo sensitivity
- · High radiant sensitivity
- · Suitable for visible and near infrared radiation
- · Fast response times
- Angle of half sensitivity: $\phi = \pm 60^{\circ}$
- · Package notch indicates collector
- Package matched with IR emitter series VSML3710
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- · Lead (Pb)-free reflow soldering
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- · Photo interrupters
- · Miniature switches
- Counters
- Encoders
- · Position sensors
- · Ligth sensors

PRODUCT SUMMARY			
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.1} (nm)
VEMT3700	0.5	± 60	450 to 1080

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
VEMT3700-GS08	Tape and reel	MOQ: 7500 pcs, 1500 pcs/reel	PLCC-2	
VEMT3700-GS18	Tape and reel	MOQ: 8000 pcs, 8000 pcs/reel	PLCC-2	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	AMETER TEST CONDITION		VALUE	UNIT	
Collector emitter voltage		V_{CEO}	70	V	
Emitter collector voltage		V _{ECO}	5	٧	
Collector current		Ic	50	mA	
Collector peak current	$t_p/T \le 0.1, t_p \le 10 \ \mu s$	I _{CM}	100	mA	
Power dissipation		P_V	100	mW	
Junction temperature		T _i	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	Acc. reflow solder profile fig. 10	T _{sd}	260	°C	
Thermal resistance junction/ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	R _{thJA}	400	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

Vishay Semiconductors Silicon NPN Phototransistor, RoHS Compliant



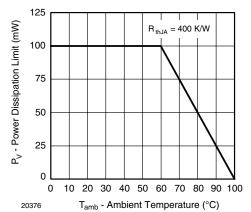


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V
Collector emitter dark current	V _{CE} = 20 V, E = 0	I _{CEO}		1	200	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		3		pF
Collector ligth current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_{CE} = 5 \text{ V}$	I _{ca}	0.25	0.5		mA
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ_{p}		850		nm
Range of spectral bandwidth		λ _{0.1}		450 to 1080		nm
Collector emitter saturation voltage	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm},$ $I_{C} = 0.1 \text{ mA}$	V _{CEsat}		0.15	0.3	V
Disa time fall time	$V_S = 5$ V, $I_C = 1$ mA, $\lambda = 950$ nm, $R_L = 1$ k Ω	t _r /t _f		6		μѕ
Rise time, fall time	$V_S = 5$ V, $I_C = 1$ mA, $\lambda = 950$ nm, $R_L = 100~\Omega$	t _r /t _f		2		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega$	f _c		180		kHz

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

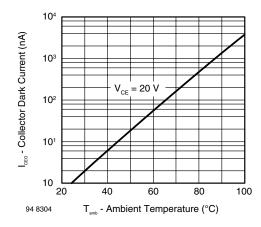


Fig. 2 - Collector Dark Current vs. Ambient Temperature

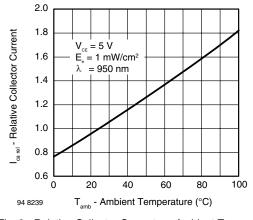


Fig. 3 - Relative Collector Current vs. Ambient Temperature



Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

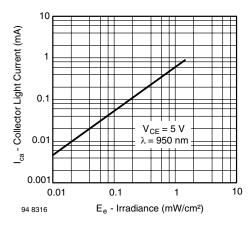


Fig. 4 - Collector Light Current vs. Irradiance

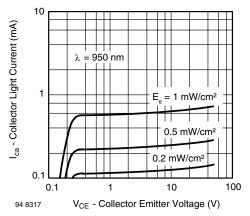


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

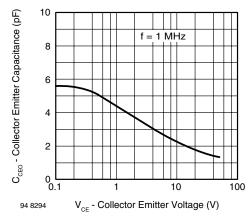


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

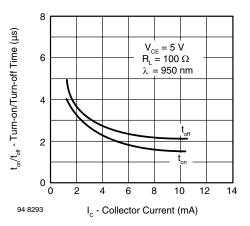


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

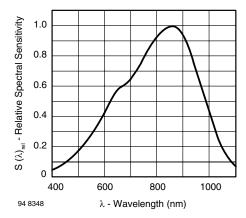


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

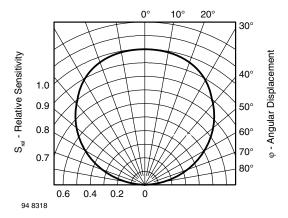
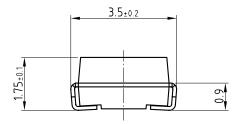


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

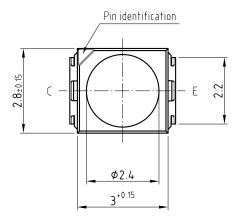
Vishay Semiconductors Silicon NPN Phototransistor, RoHS Compliant

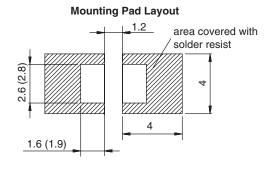


PACKAGE DIMENSIONS in millimeters









Drawing-No.: 6.541-5067.03-4 Issue: 1; 30.05.07

20873

SOLDER PROFILE

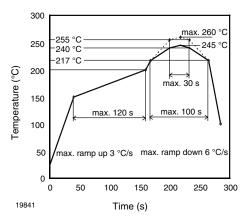


Fig. 10 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

Conditions: T_{amb} < 30 °C, RH < 60 %

Moisture sensitivity level 2a, acc. to J-STD-020.

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 $^{\circ}$ C (+ 5 $^{\circ}$ C), RH < 5 $^{\circ}$ M.



Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

TAPE AND REEL

PLCC-2 components are packed in antistatic blister tape (DIN IEC (CO) 564) for automatic component insertion. Cavities of blister tape are covered with adhesive tape.

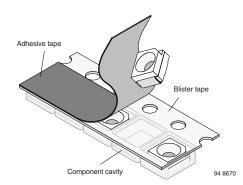


Fig. 11 - Blister Tape

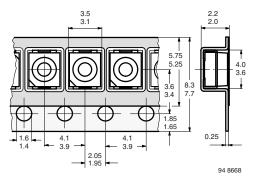


Fig. 12 - Tape Dimensions in mm for PLCC-2

MISSING DEVICES

A maximum of 0.5 % of the total number of components per reel may be missing, exclusively missing components at the beginning and at the end of the reel. A maximum of three consecutive components may be missing, provided this gap is followed by six consecutive components.

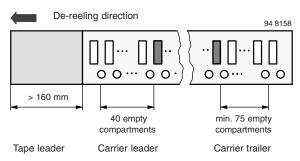


Fig. 13 - Beginning and End of Reel

The tape leader is at least 160 mm and is followed by a carrier tape leader with at least 40 empty compartments. The tape leader may include the carrier tape as long as the cover tape is not connected to the carrier tape. The least component is followed by a carrier tape trailer with a least 75 empty compartments and sealed with cover tape.

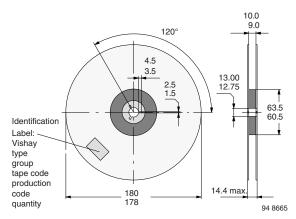


Fig. 14 - Dimensions of Reel-GS08

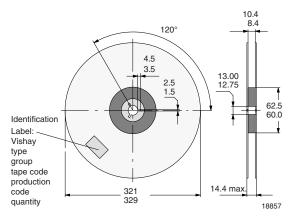


Fig. 15 - Dimensions of Reel-GS18

COVER TAPE REMOVAL FORCE

The removal force lies between 0.1 N and 1.0 N at a removal speed of 5 mm/s. In order to prevent components from popping out of the blisters, the cover tape must be pulled off at an angle of 180° with regard to the feed direction.



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Revision: 18-Jul-08

Document Number: 91000 www.vishay.com